

F-1 G. 1

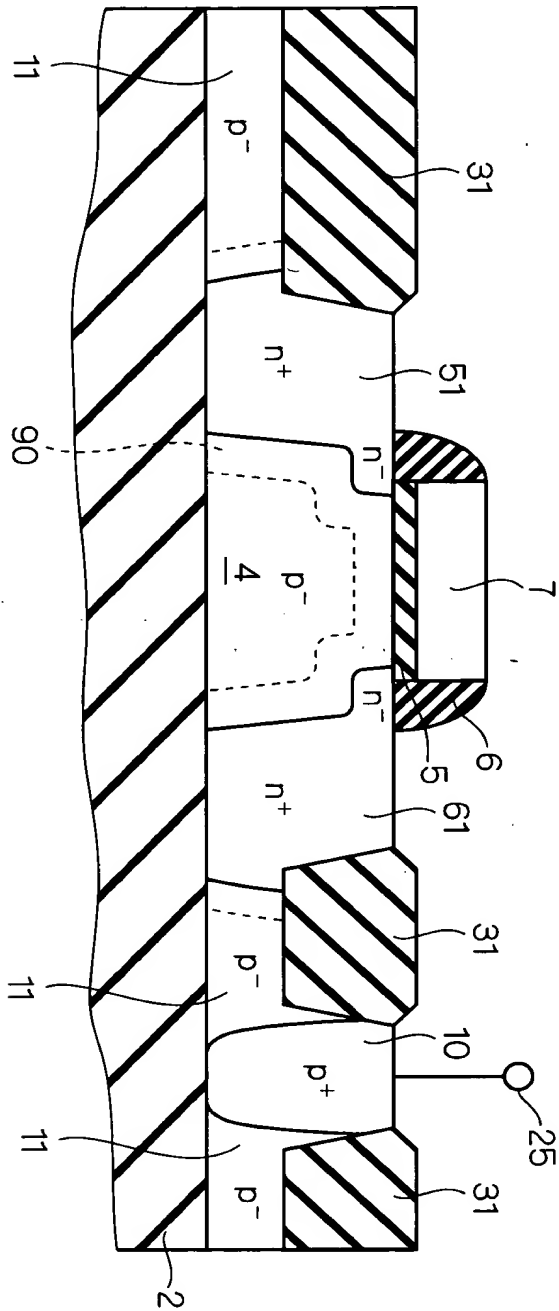


FIG. 2

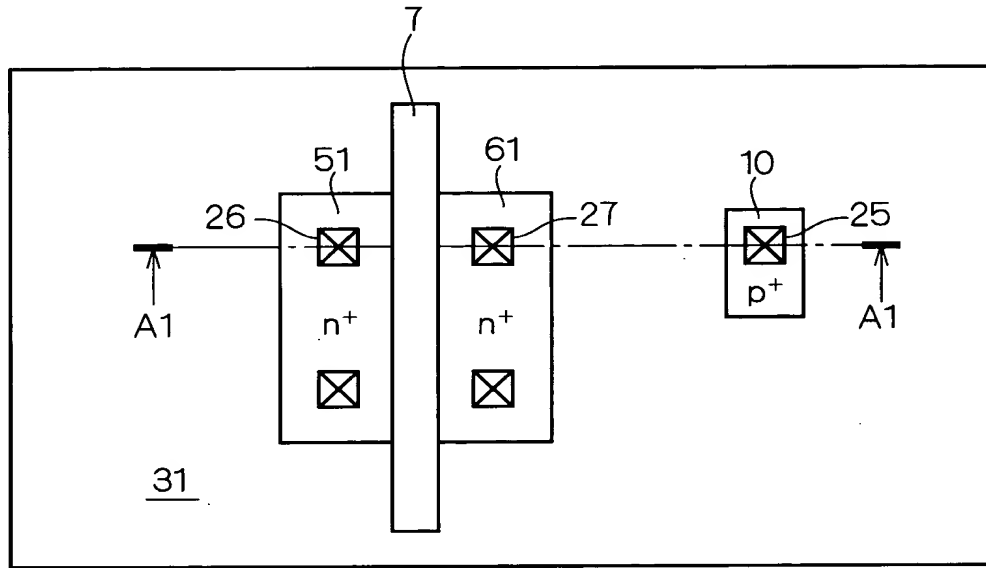
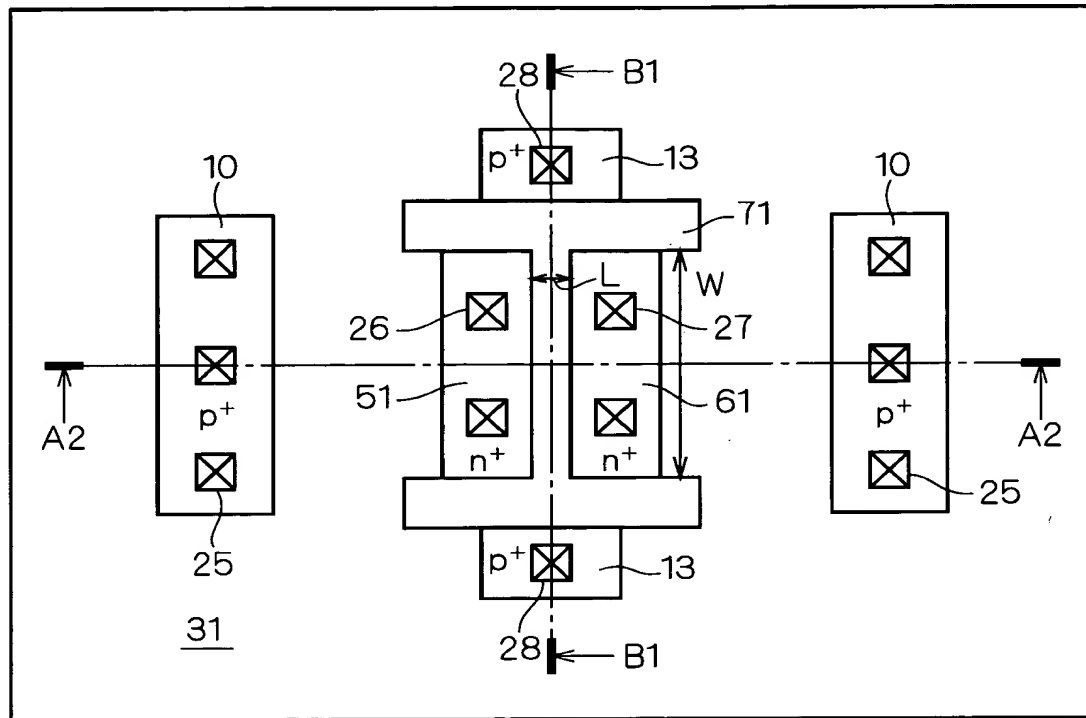


FIG. 2

FIG. 3

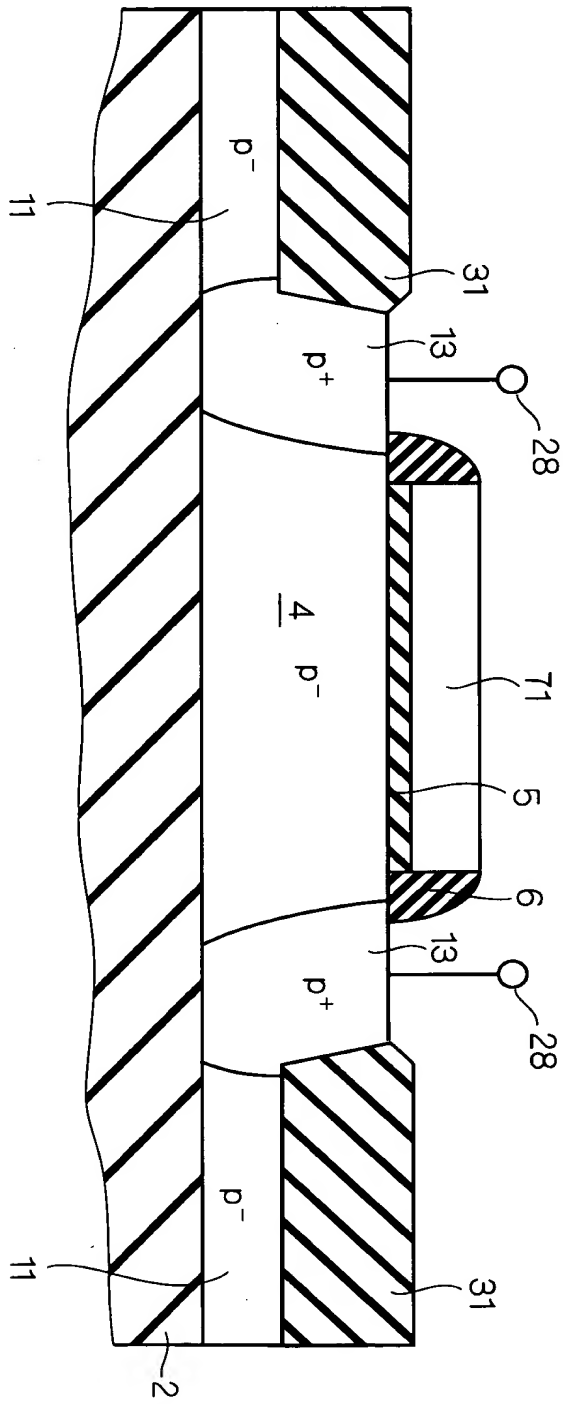


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[illegible]

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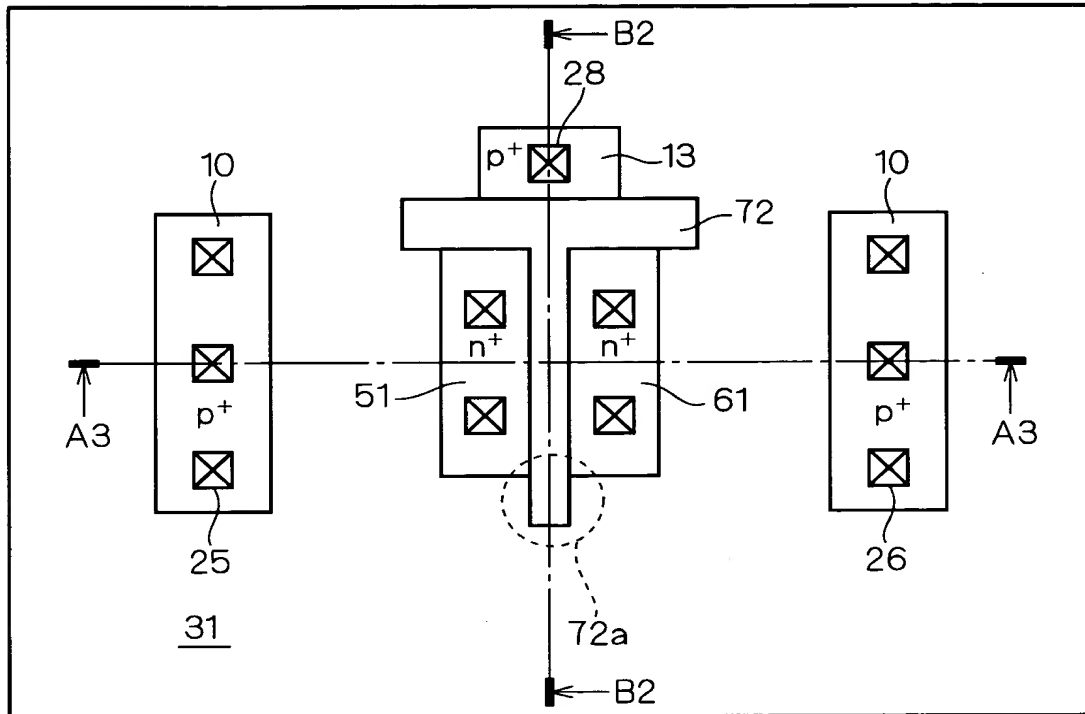
FIG. 5



This diagram shows a cross-section of a semiconductor device. The substrate consists of alternating layers of p⁺ and p⁻ material. A central channel or well contains n⁺ and n⁻ regions. Various electrical contacts are shown: 10 (top surface), 31 (sidewall), 52 (bottom contact), 6 (edge contact), 7 (top contact), 91 (side contact), and R1 (resistor-like structures). The device is also labeled with 11 and 2.

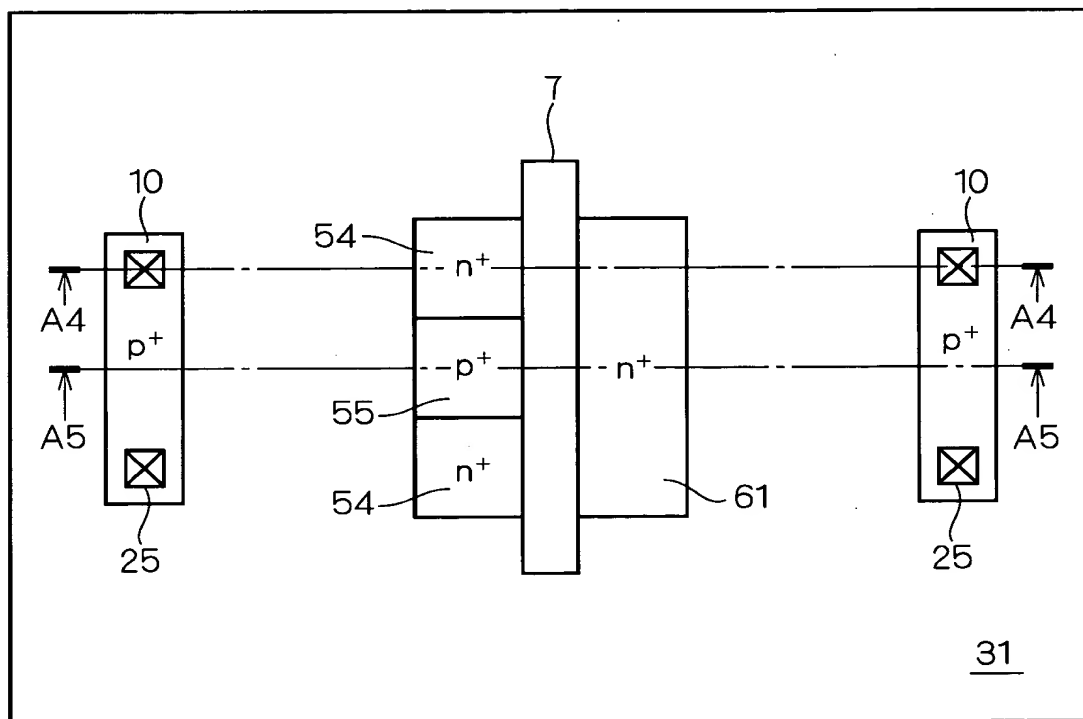
[illegible]

FIG. 9



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FIG. 10



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FIG. 11

FIG. 11

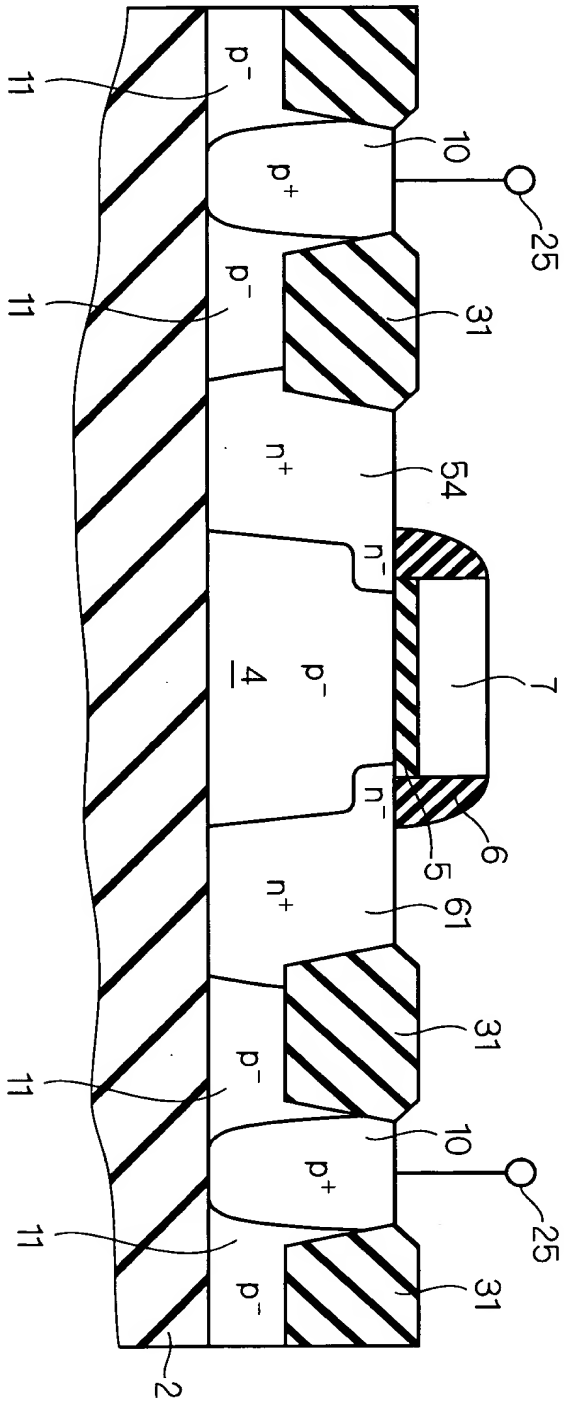


FIG. 12

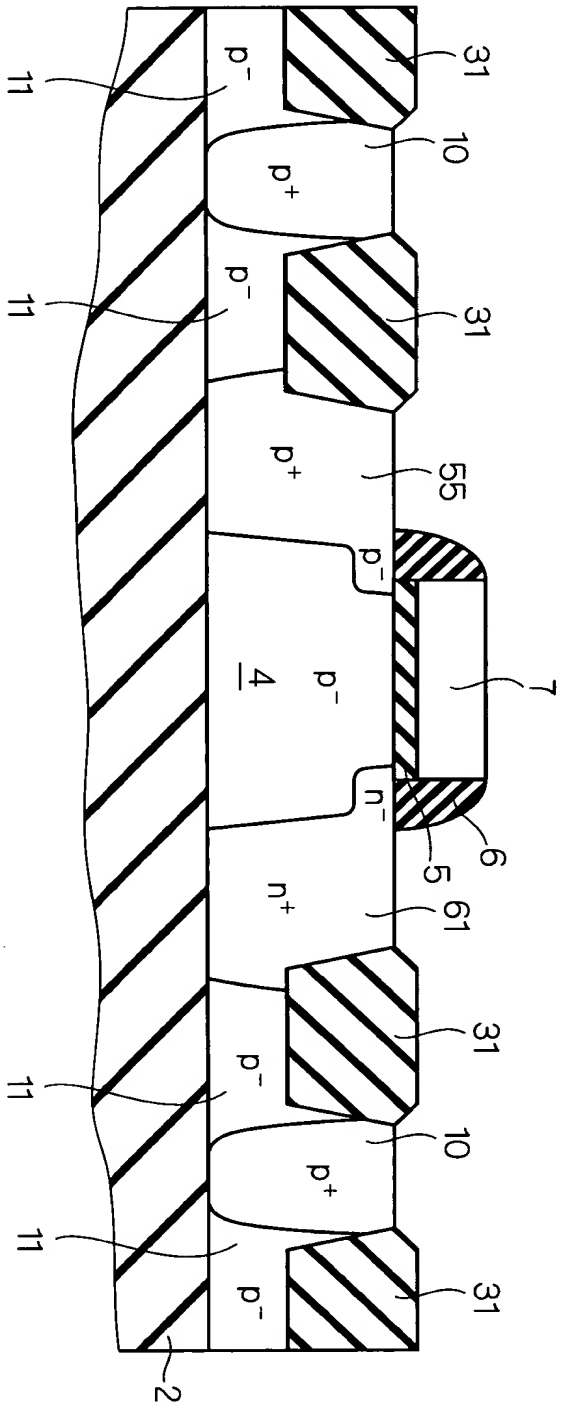
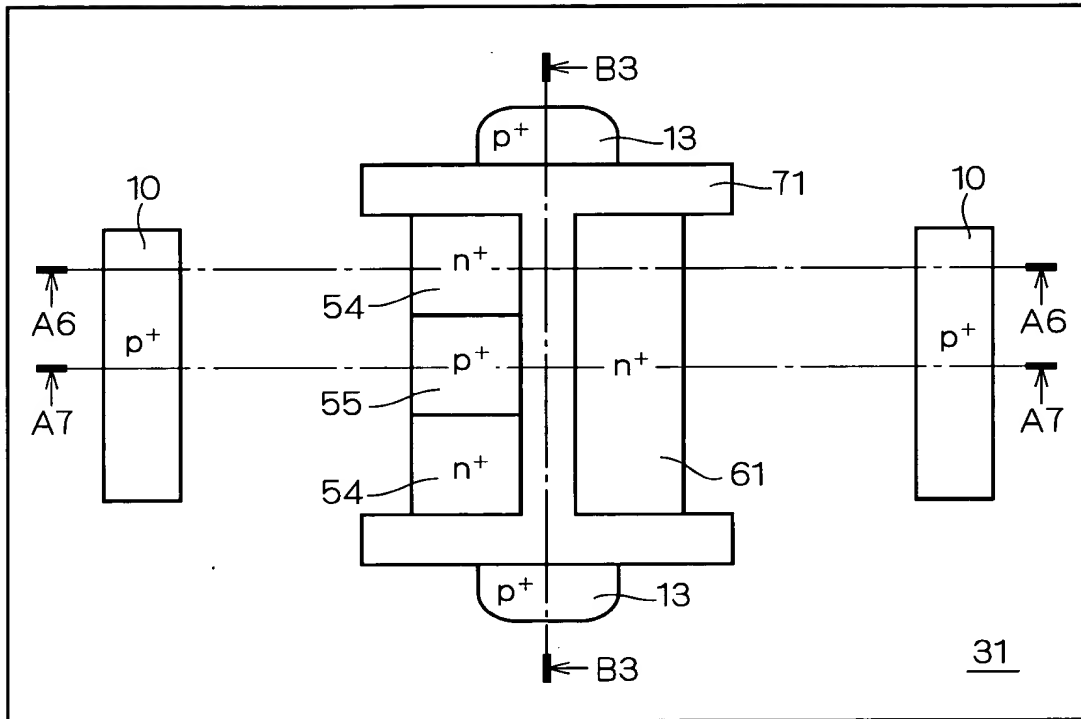
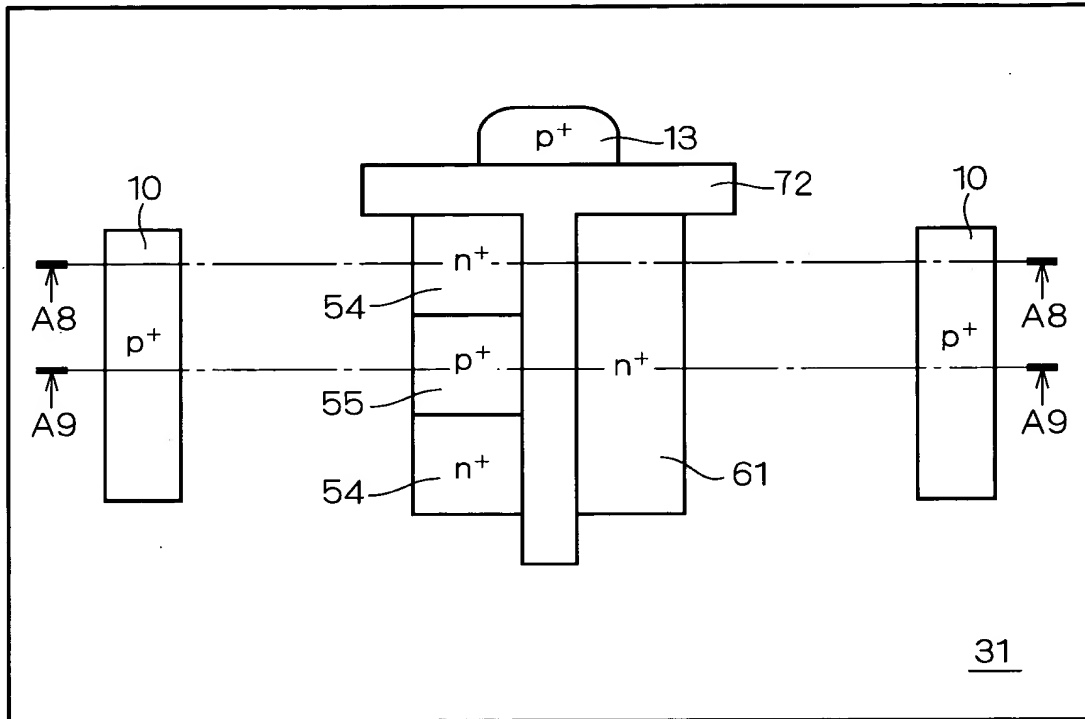


FIG. 13



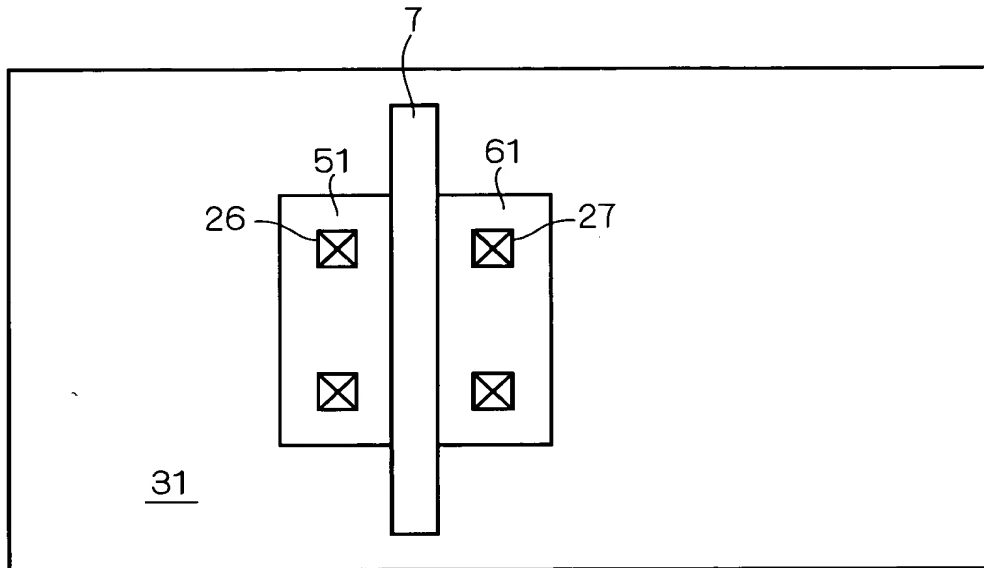
09986004-110701

FIG. 14



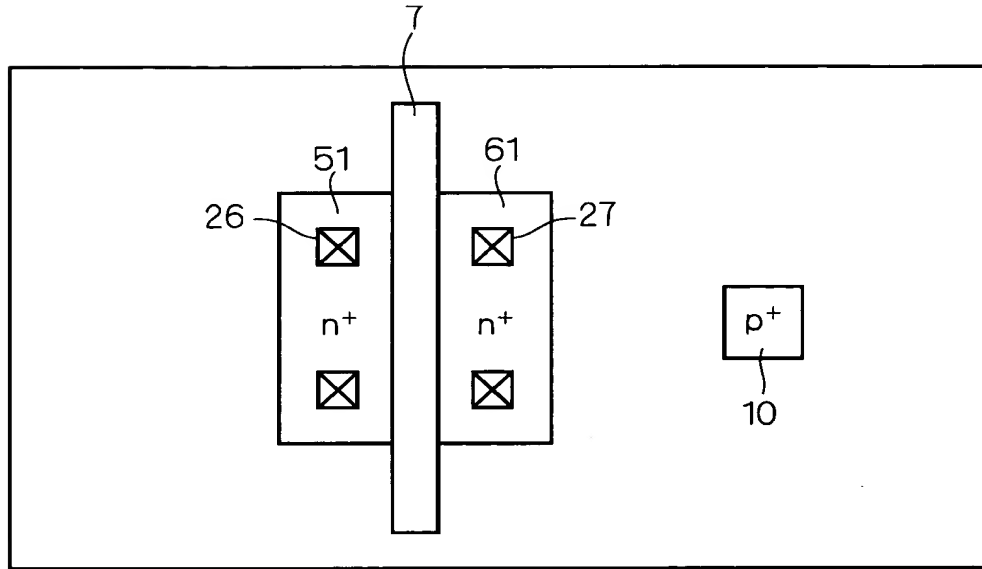
09386004-110701

FIG. 16



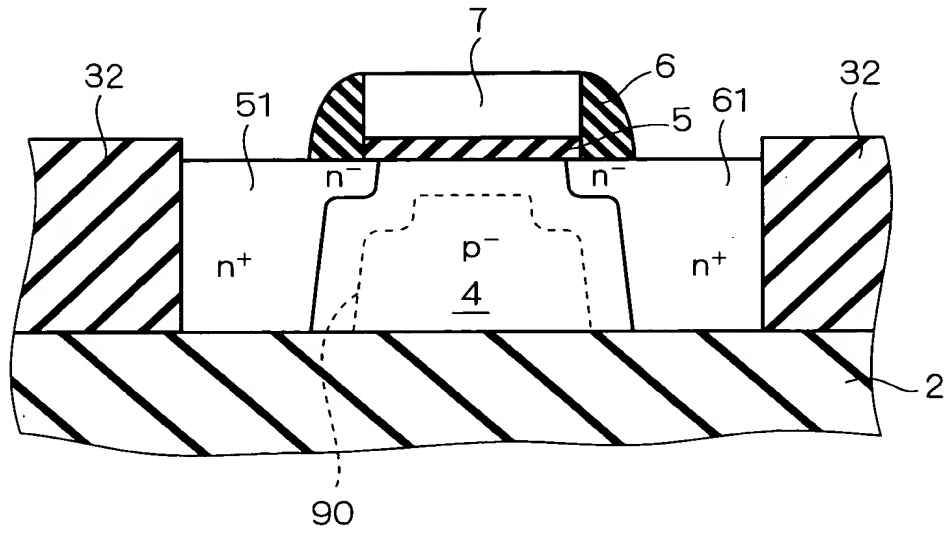
09085004-110701

F I G . 1 7



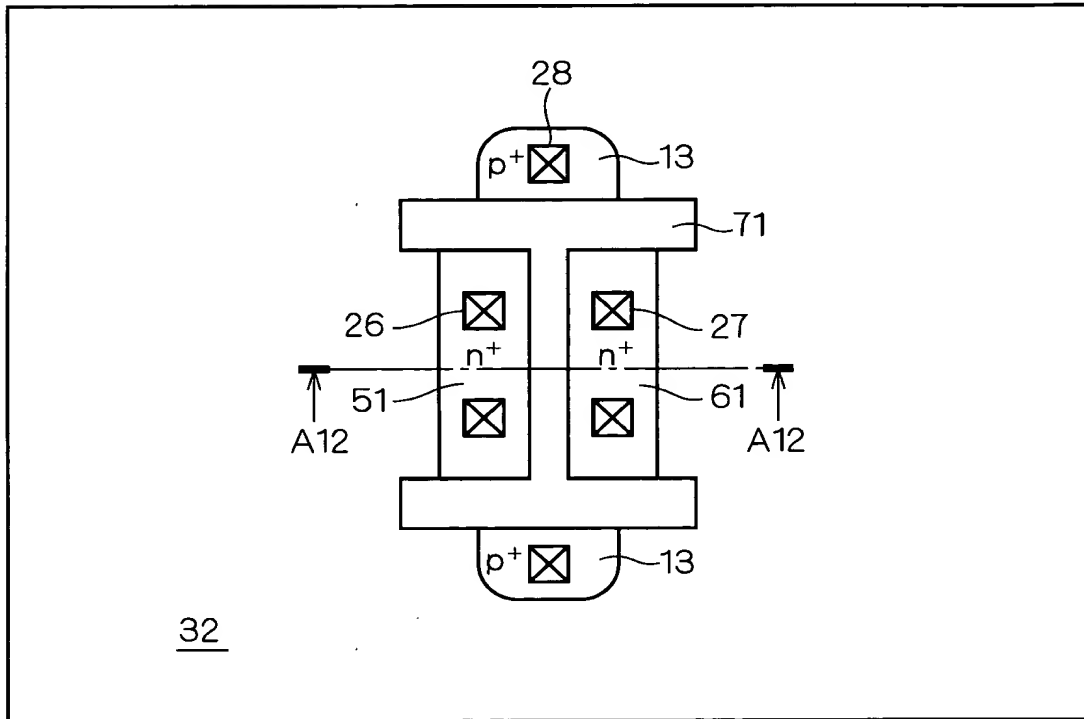
09986004-110701

F I G . 1 8



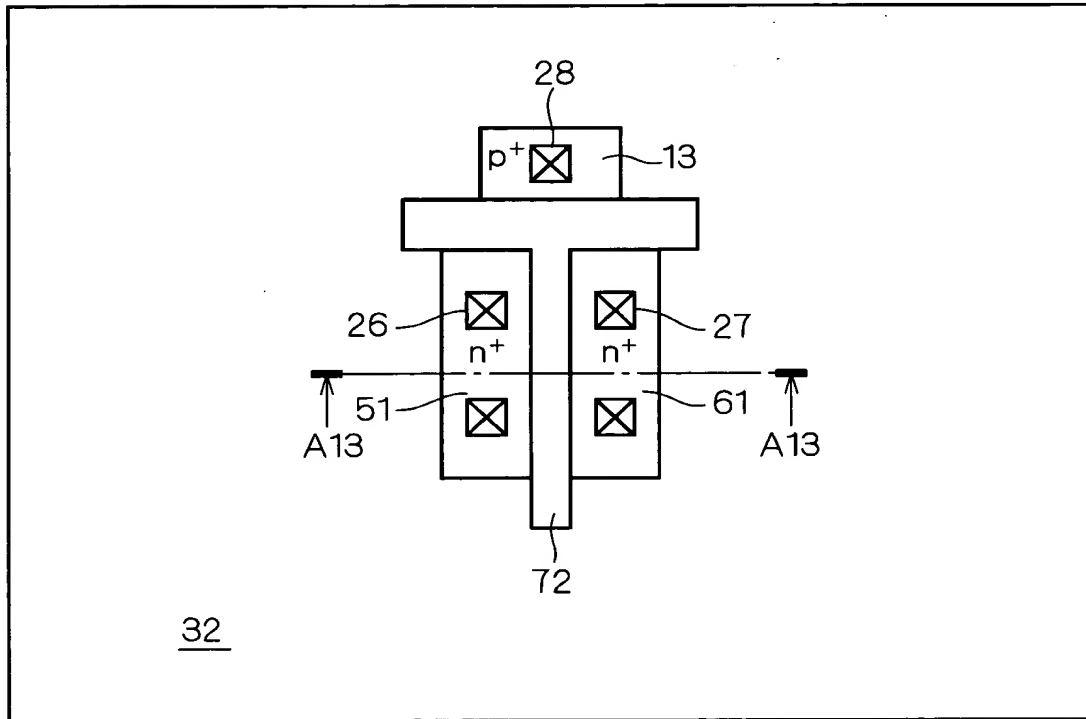
09986004-110701

FIG. 19



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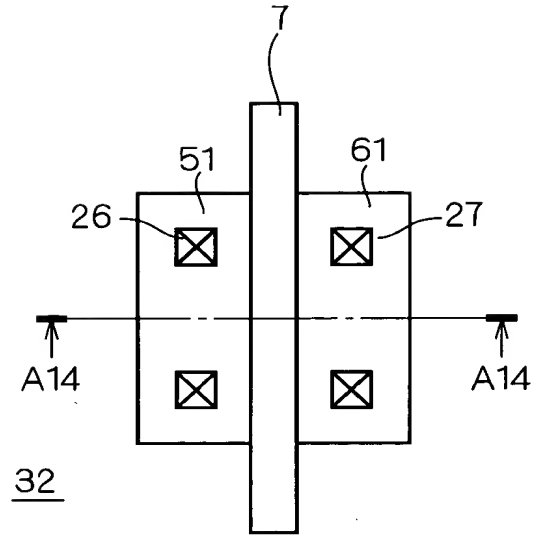
FIG. 20



32

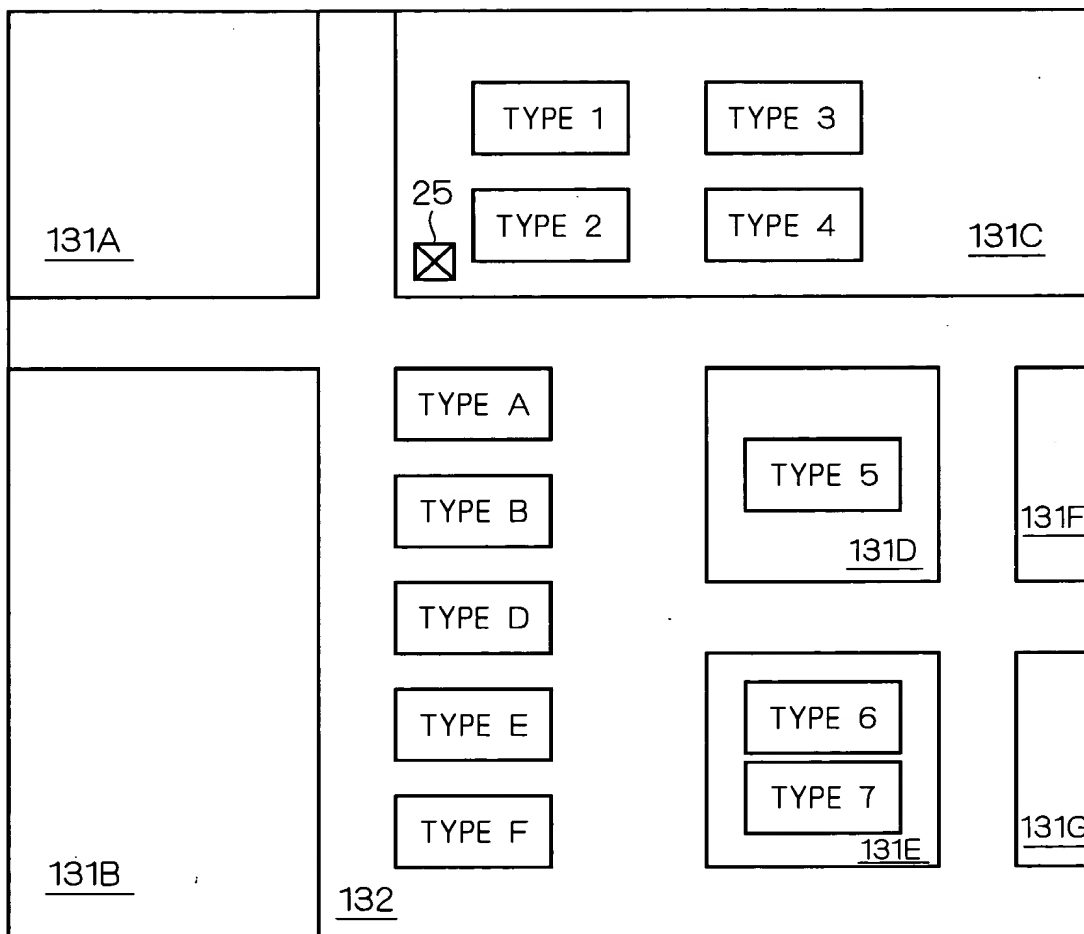
09986004.110701

F I G . 2 1



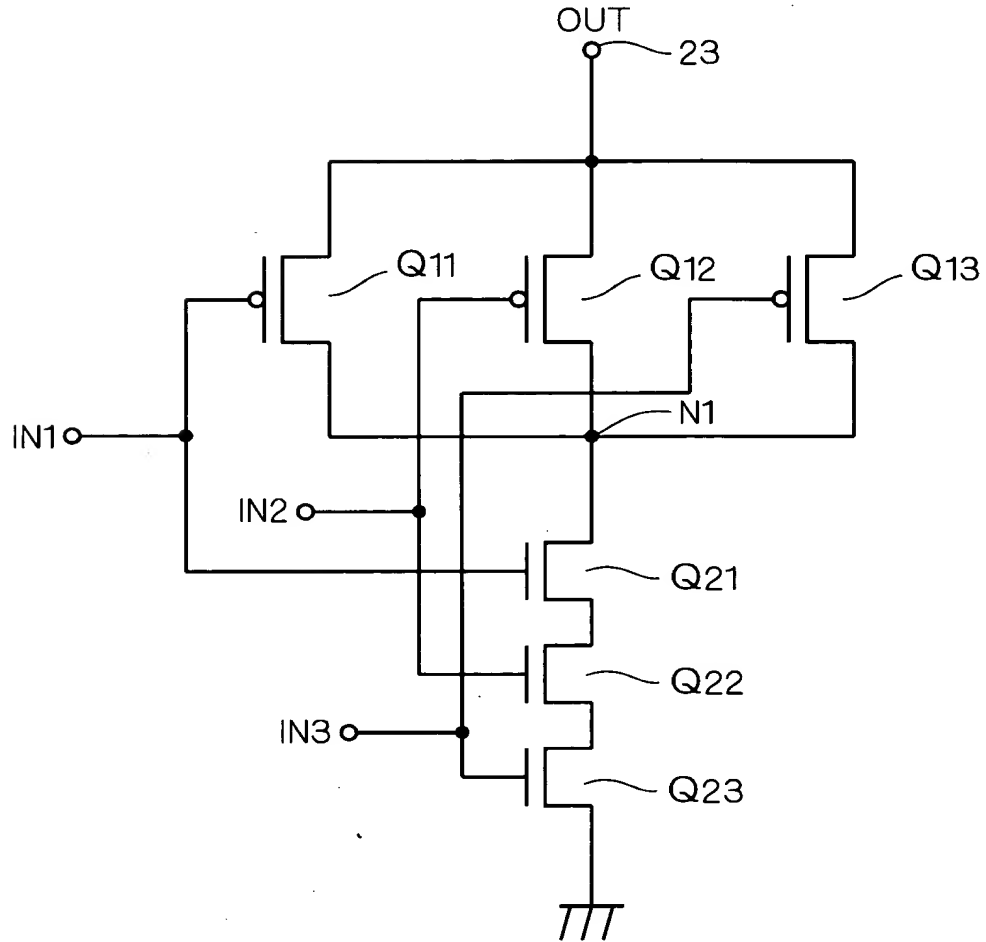
09986004.110701

F I G . 2 2



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FIG. 23



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FIG. 24

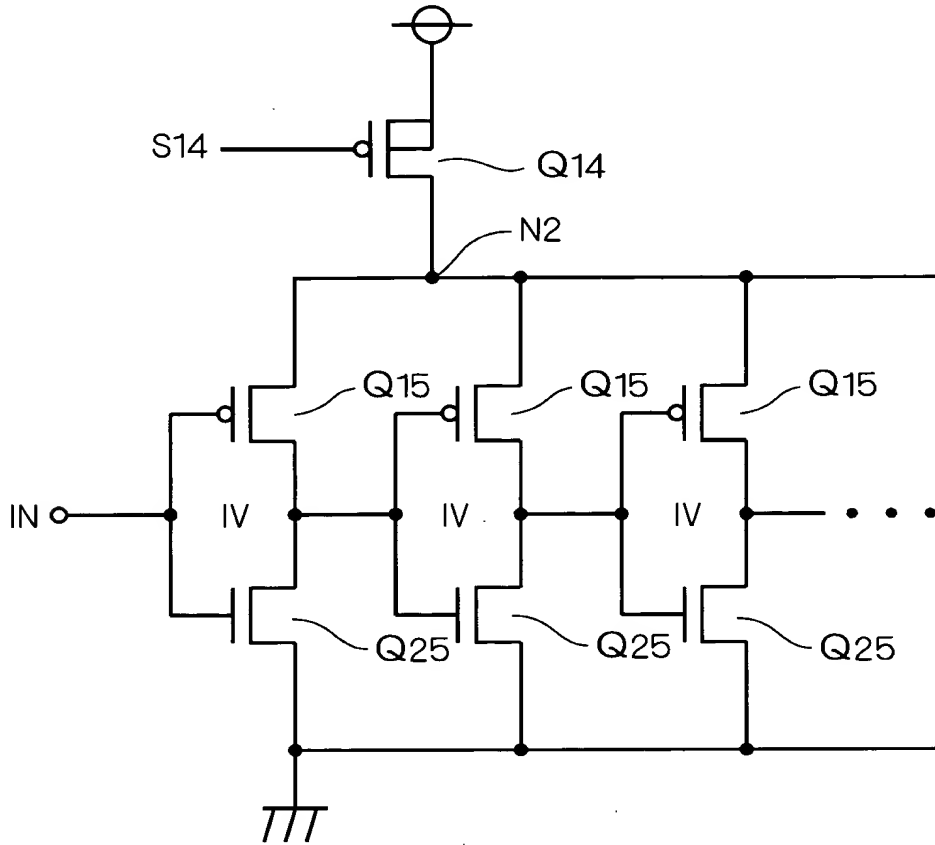
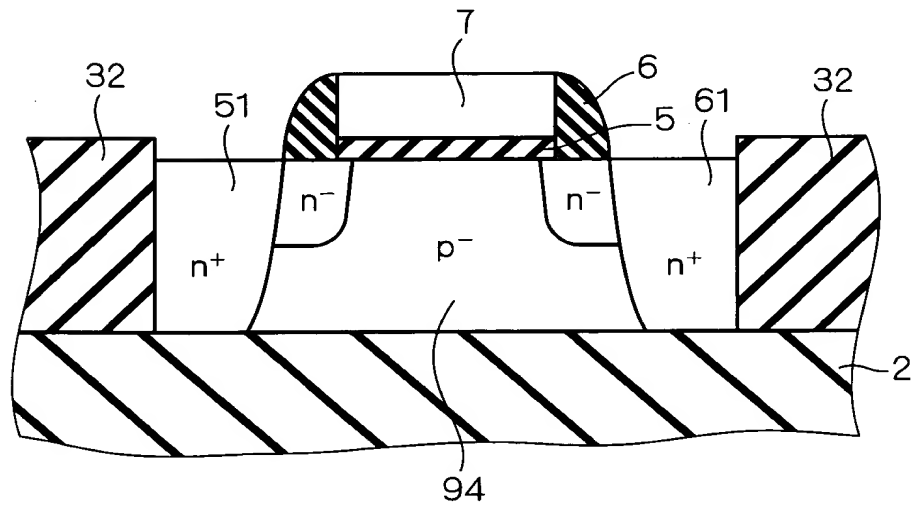
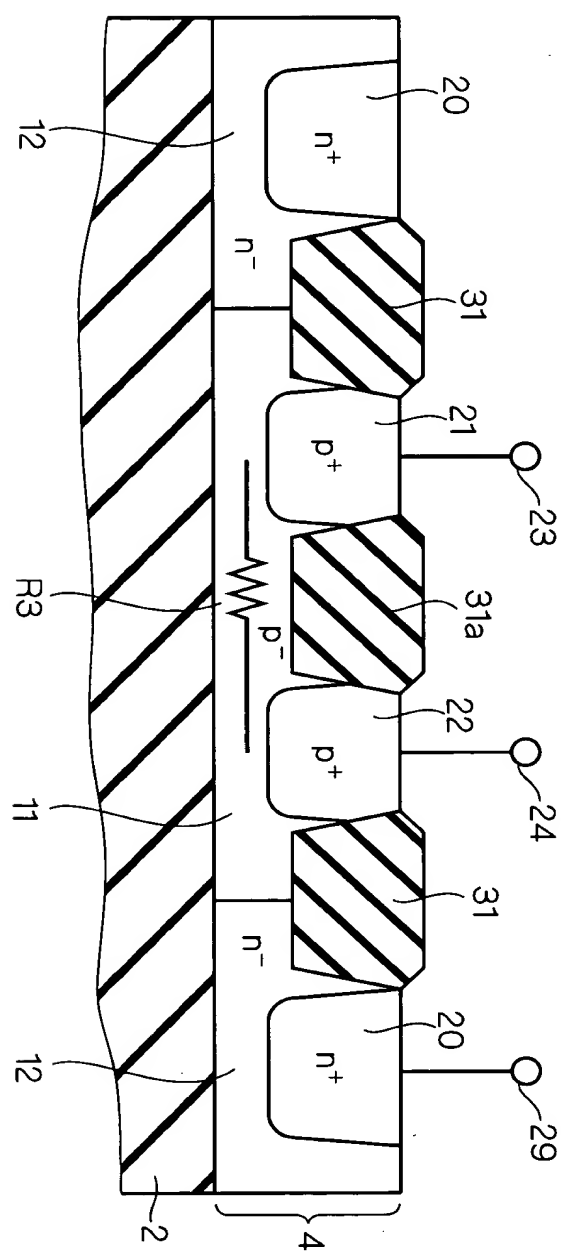


FIG. 25



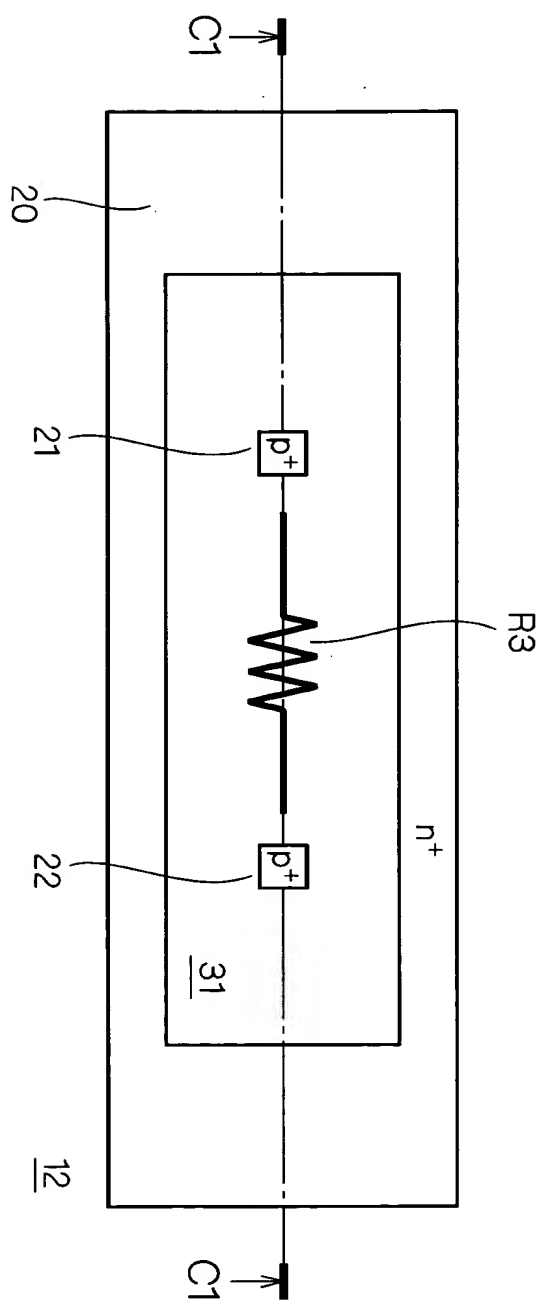
104011-40098660

FIG. 26



104011740098660

FIG. 27



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FIG. 28

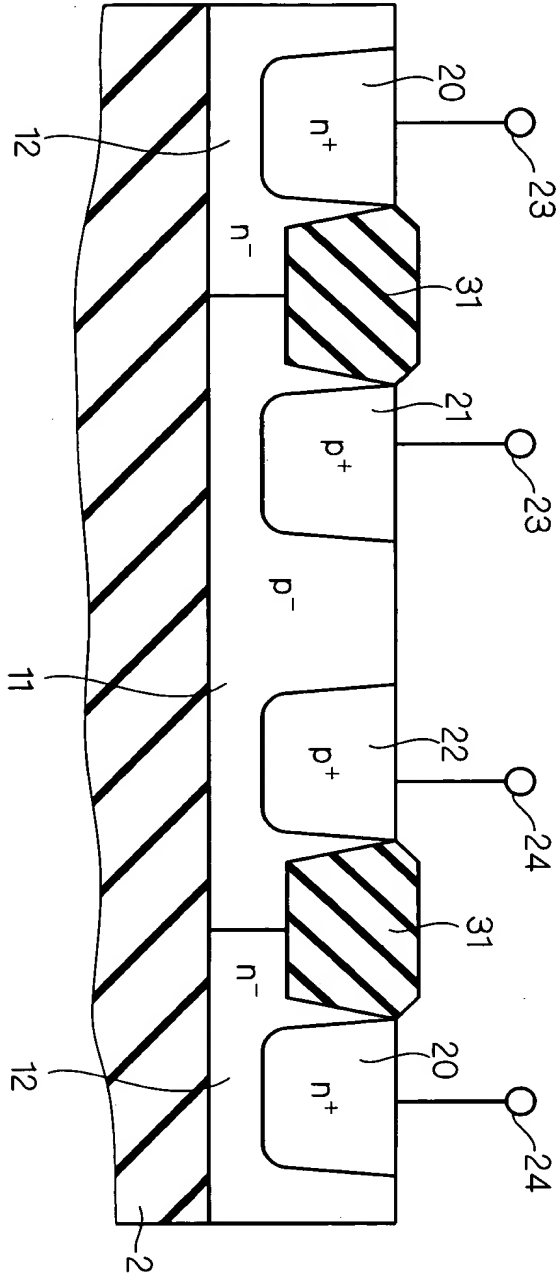


FIG. 30

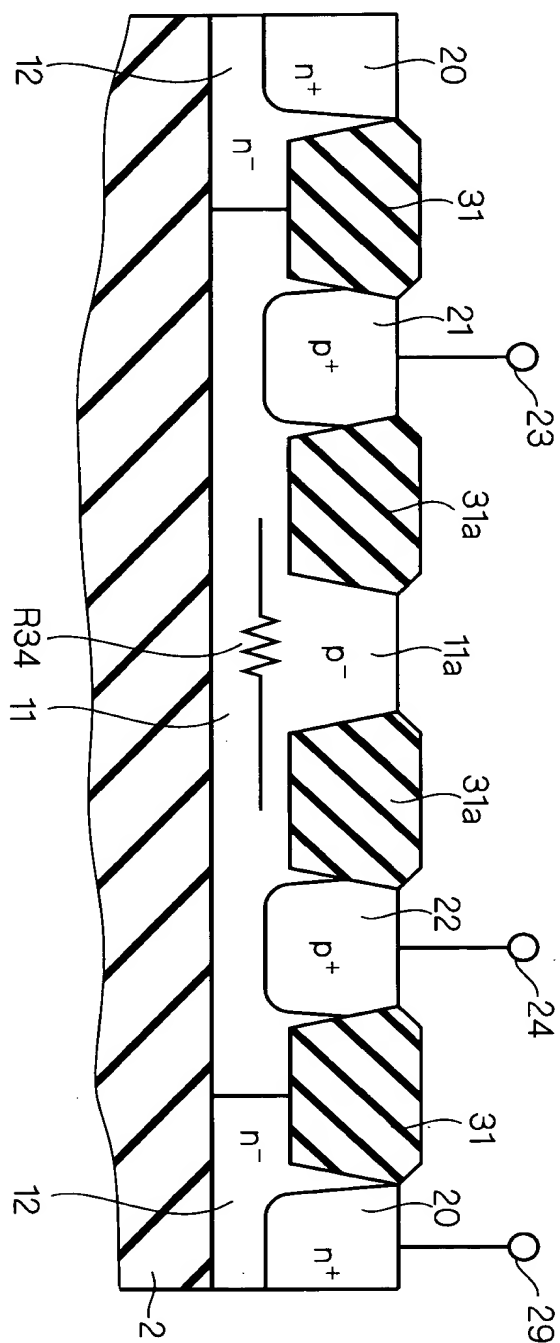
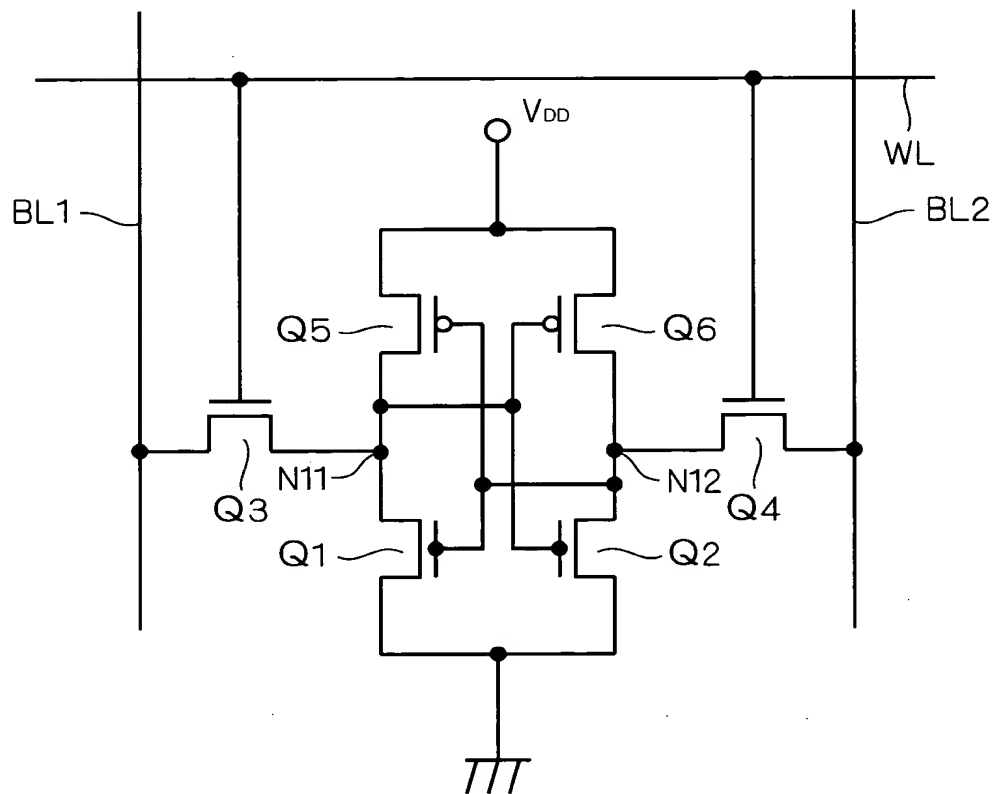


FIG. 31



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FIG. 32

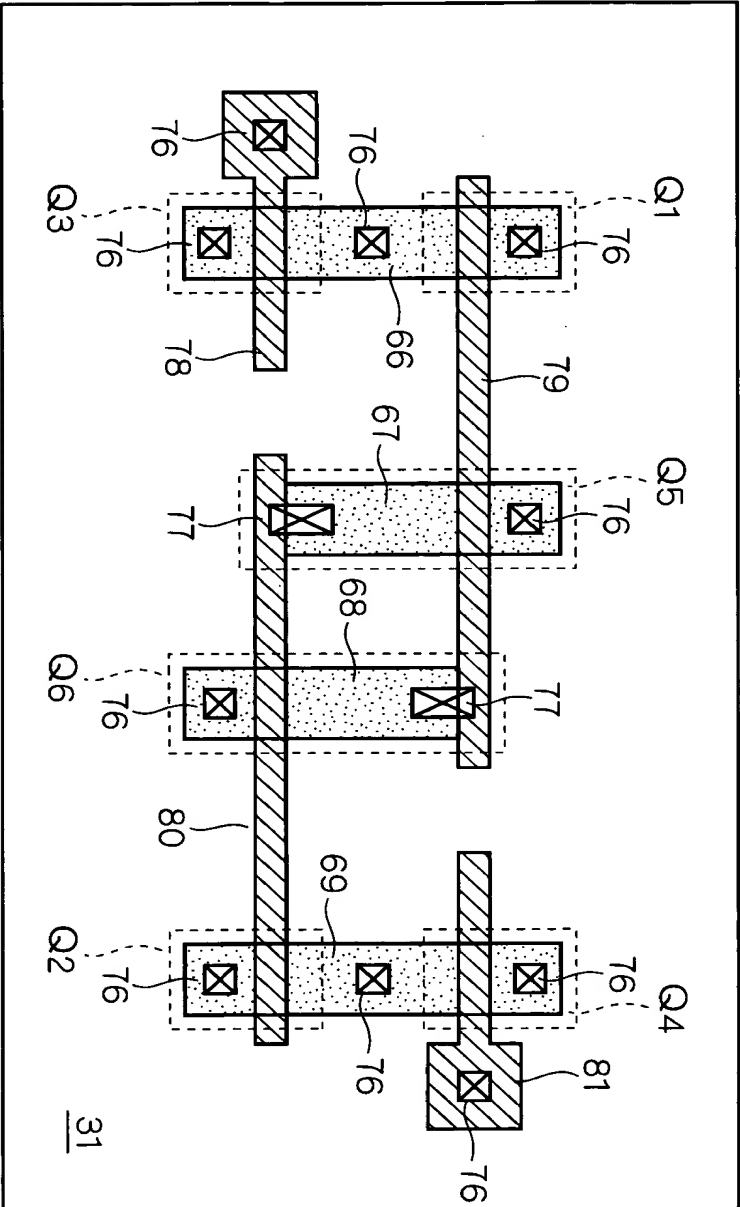


FIG. 33

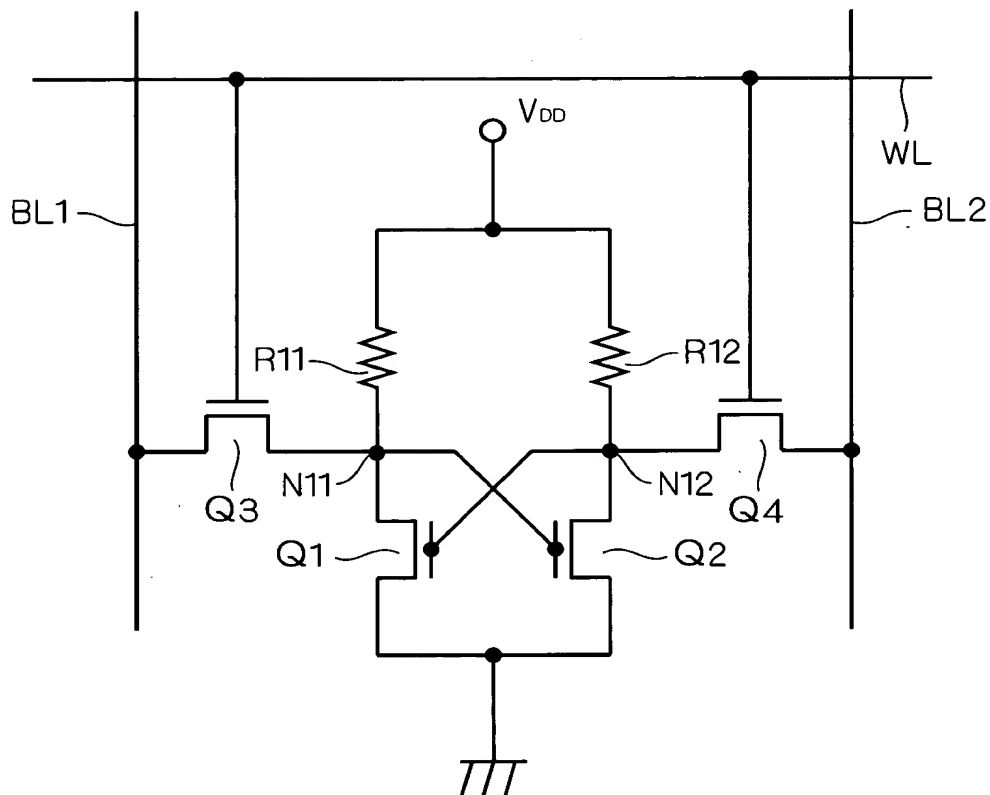


FIG. 33

FIG. 34

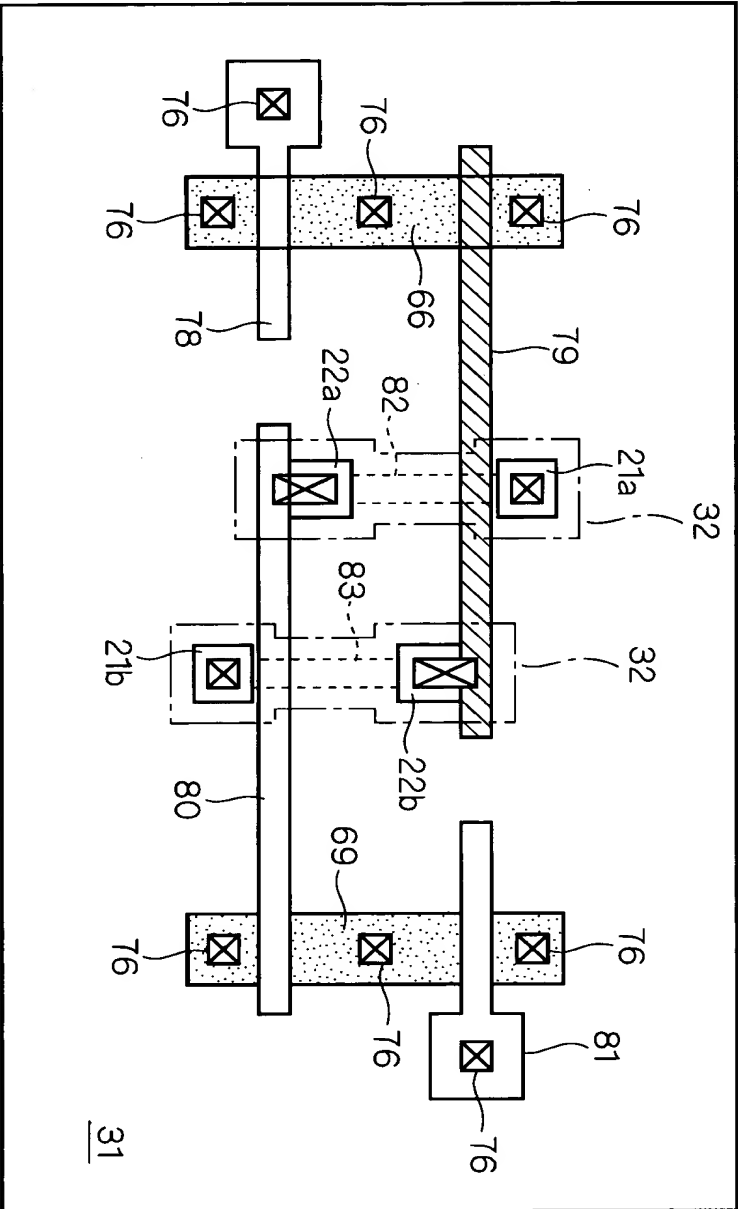


FIG. 36

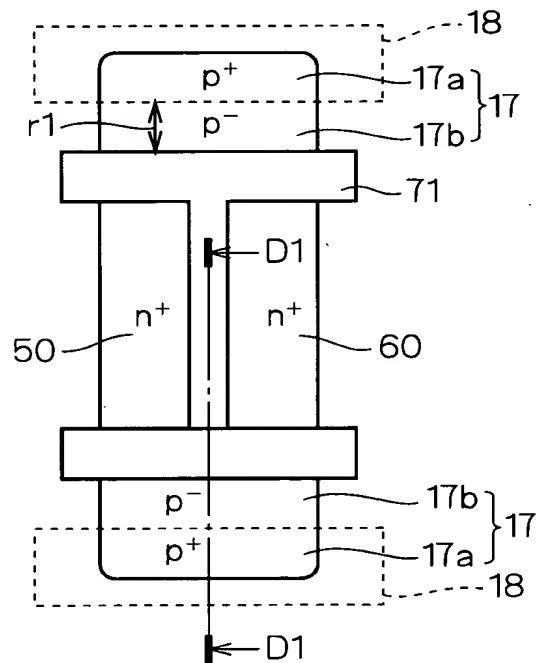
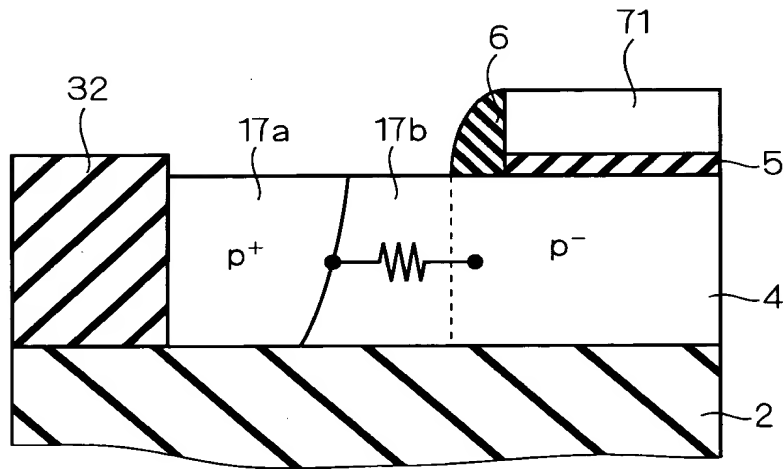


FIG. 37



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FIG. 38

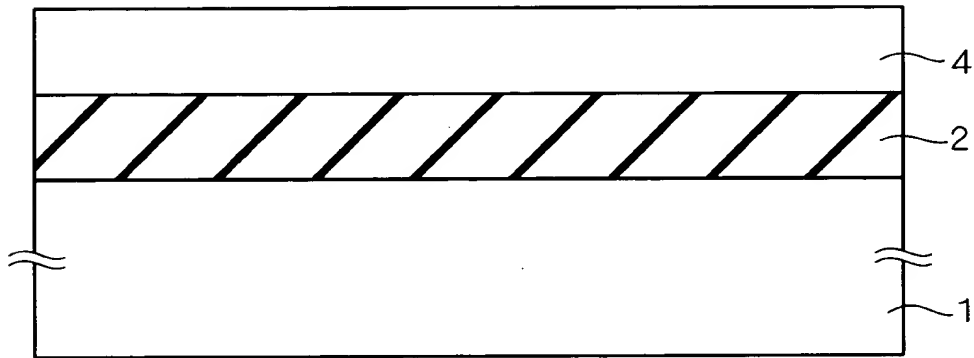
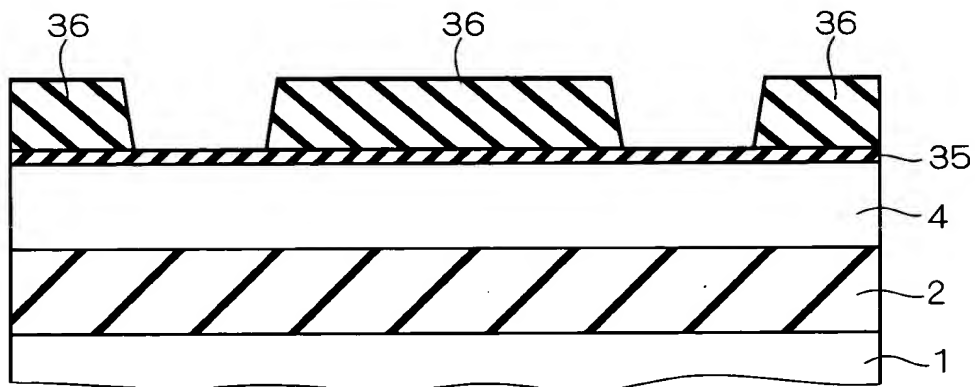


FIG. 39



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FIG. 40

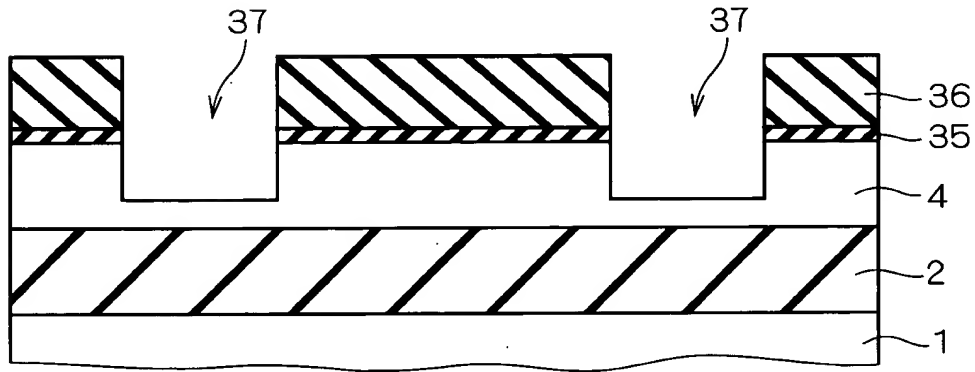
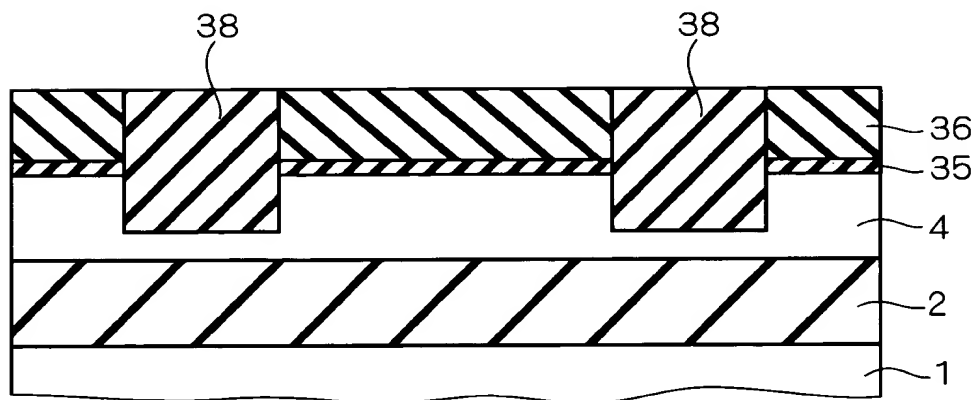
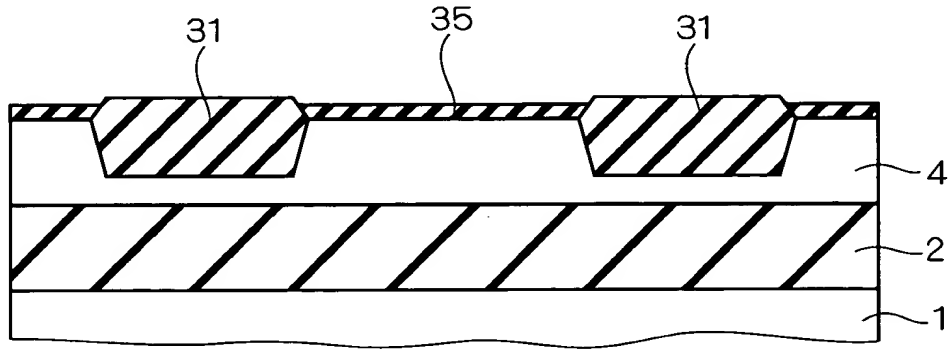


FIG. 41



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FIG. 42

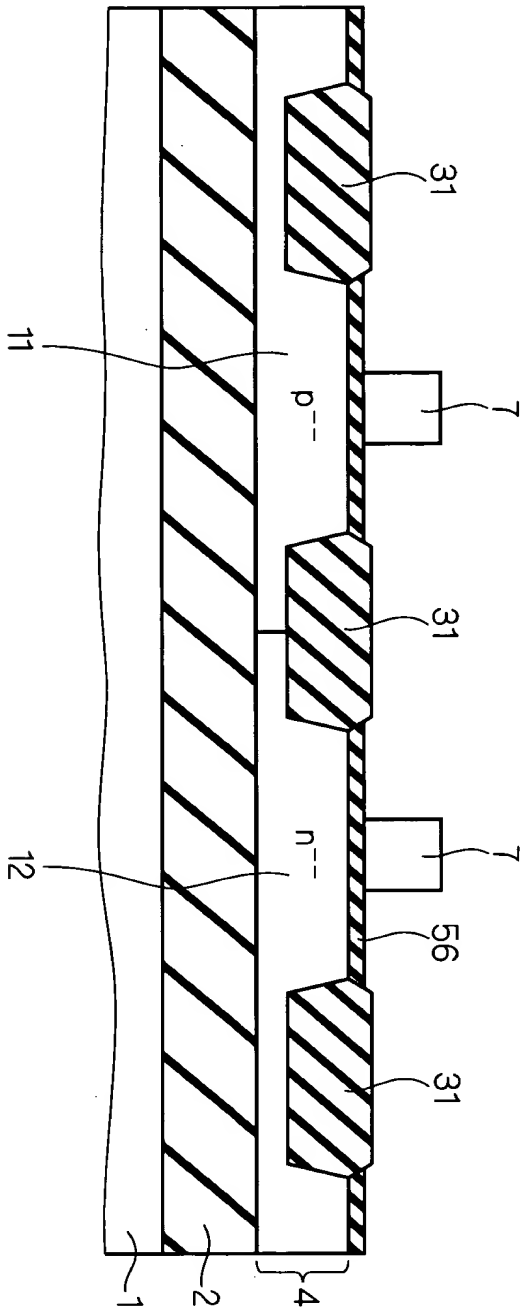


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This cross-sectional view shows a substrate 1 with a patterned layer 2. A layer 4 is formed on top of layer 2, with openings 31. A top layer 11 is shown above layer 4, with a gap 40 between it and layer 4. Arrows indicate a process step, possibly etching or deposition, occurring in the gap 40.

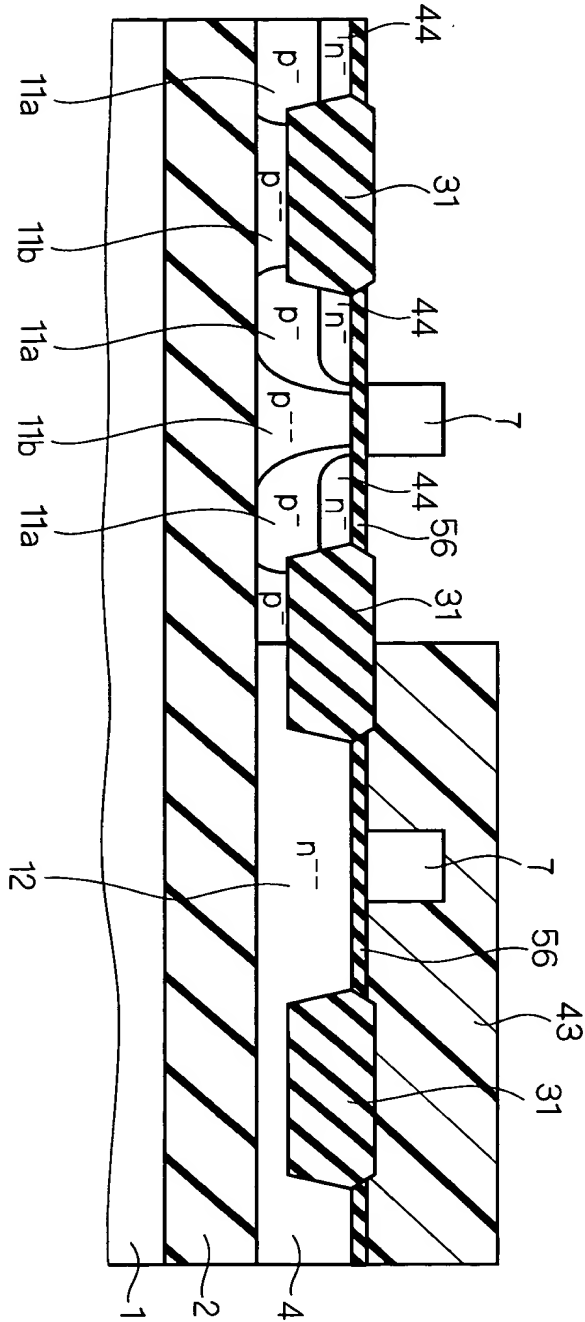
10,201,100,936,60

FIG. 45



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FIG. 46



FOOT-10098660

FIG. 47

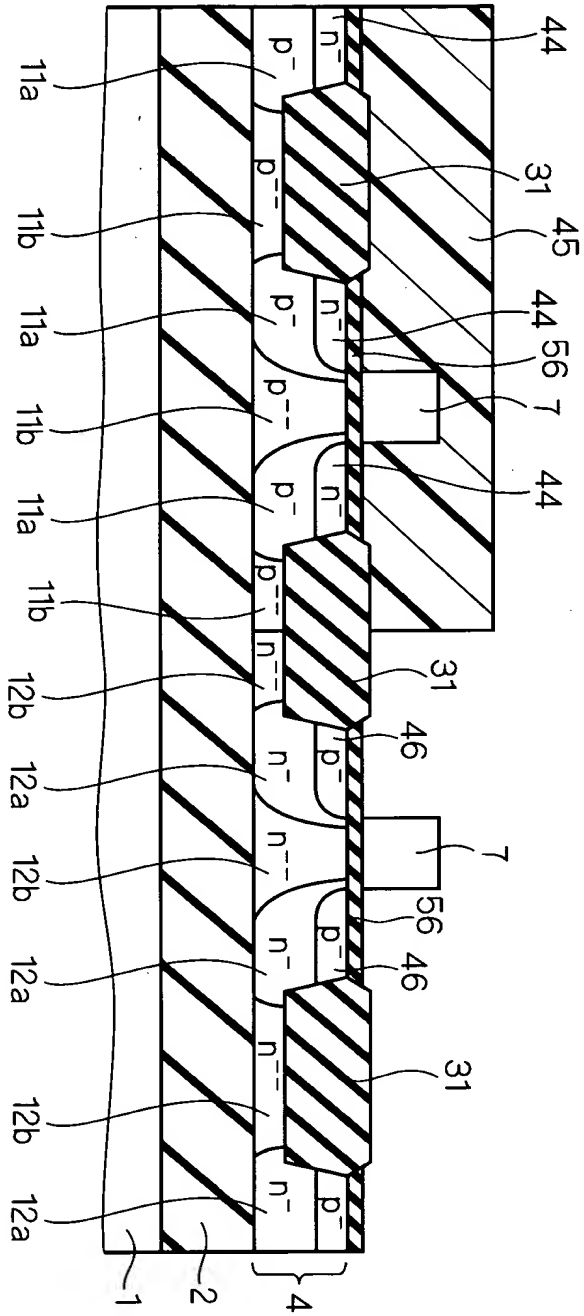


FIG. 48

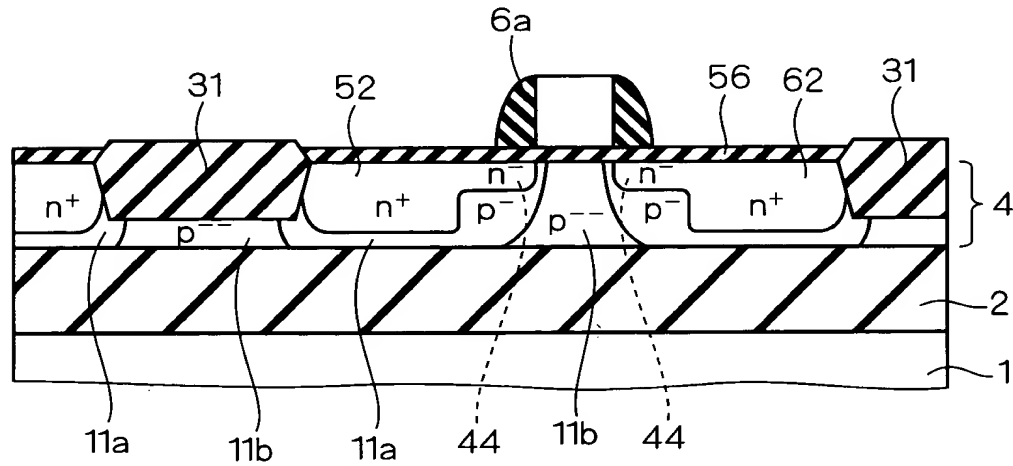
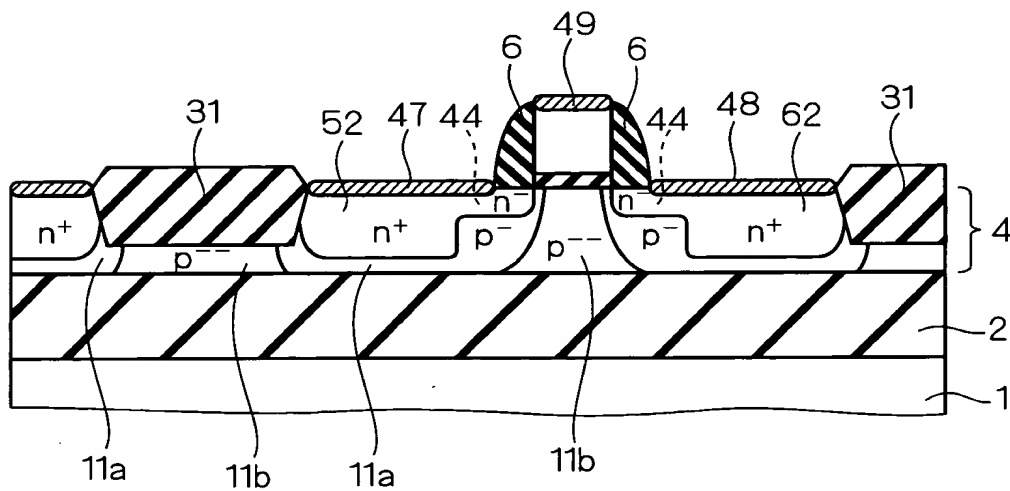


FIG. 49



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FIG. 50

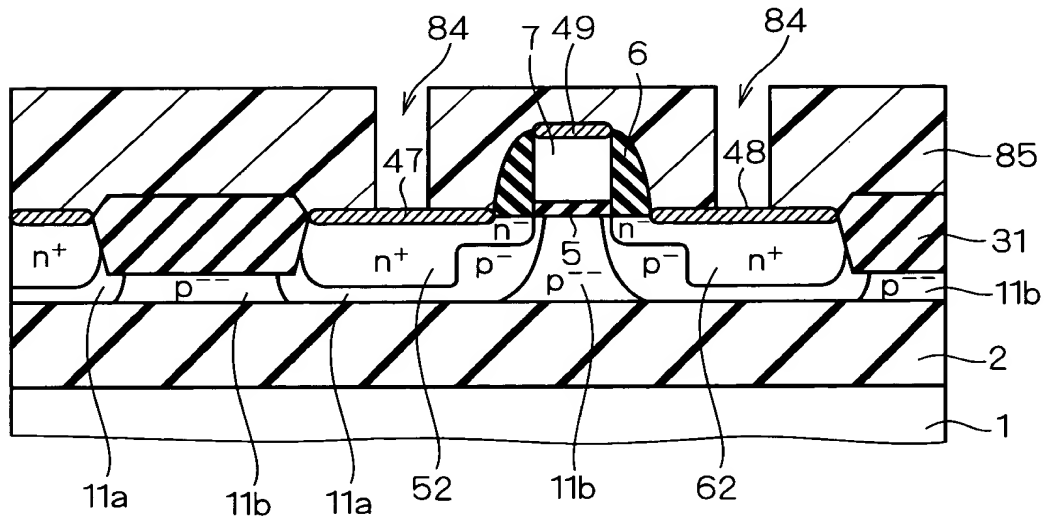


FIG. 51

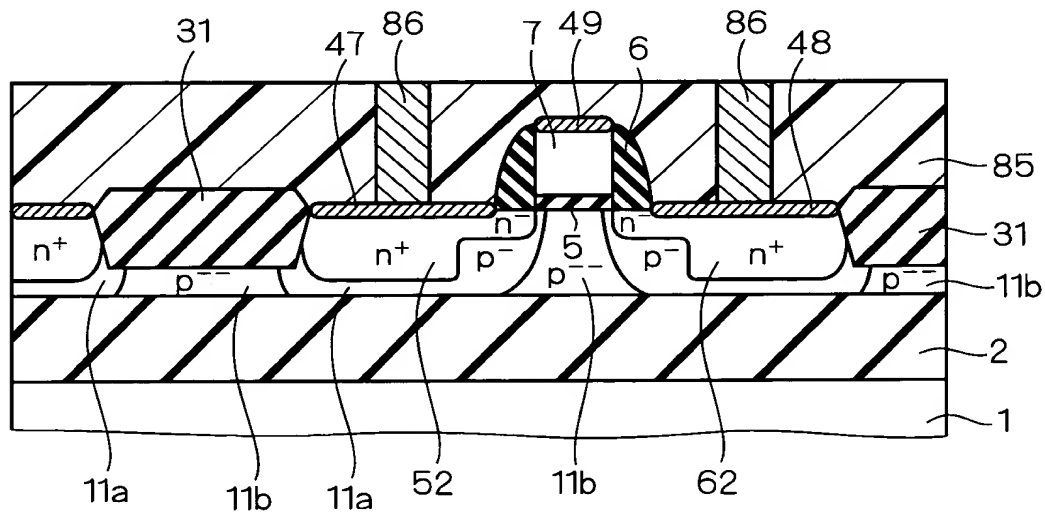


FIG. 50

[illegible]

FIG. 54

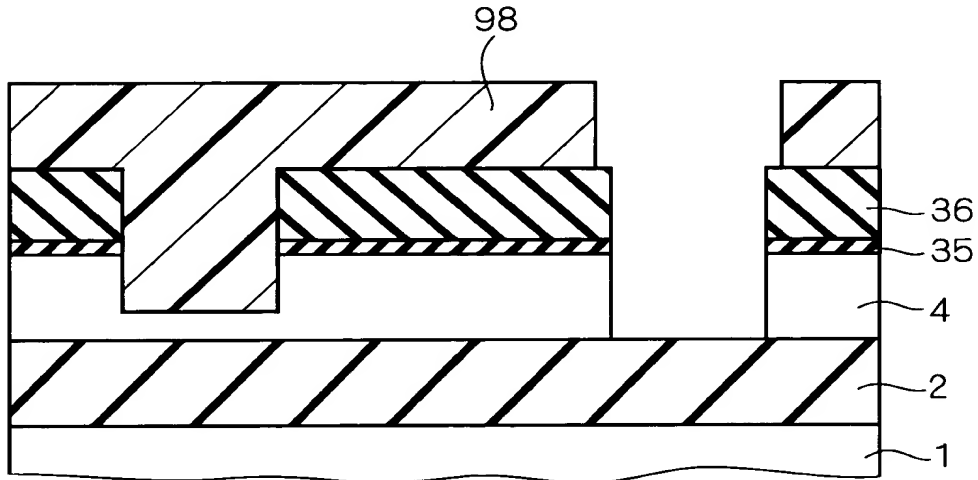
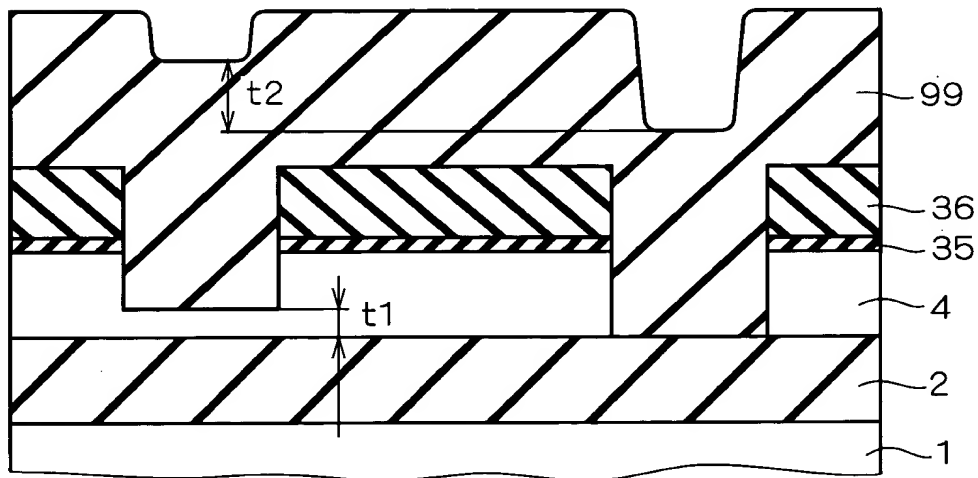


FIG. 55



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FIG. 56

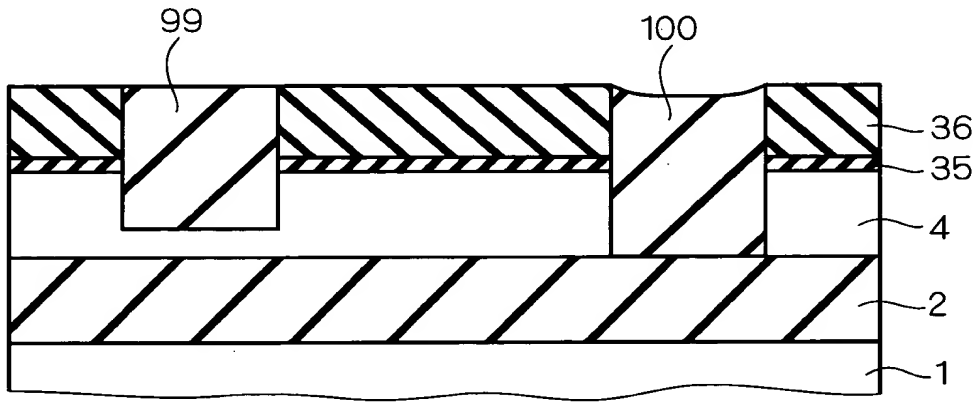
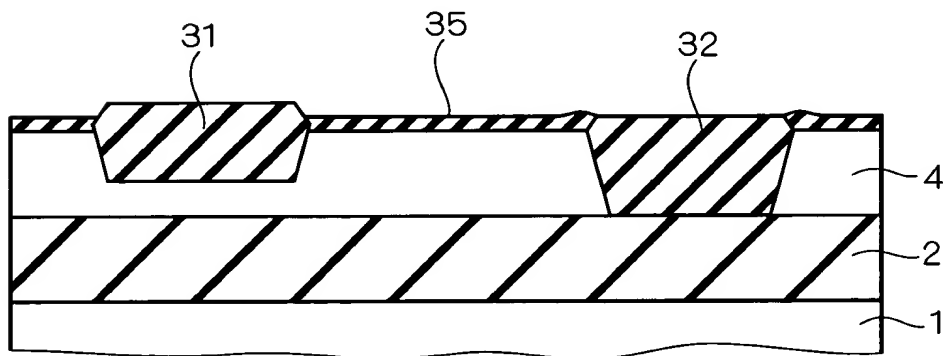


FIG. 57



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FIG. 58

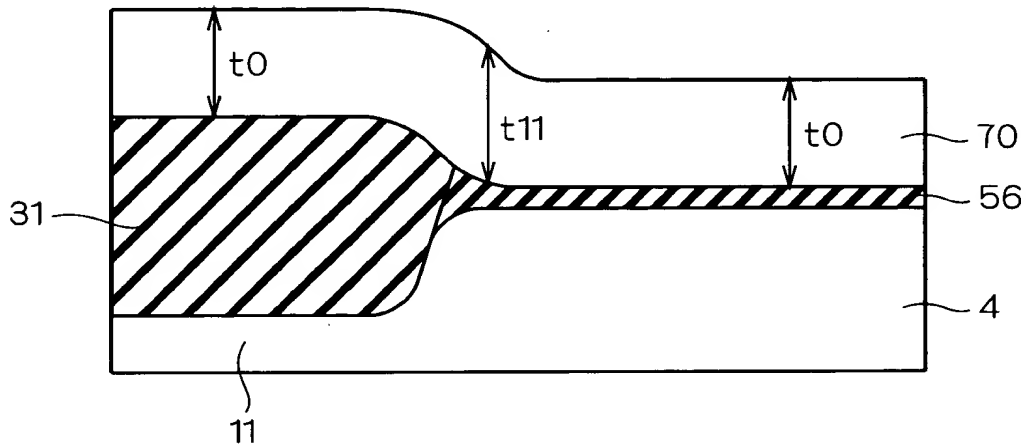
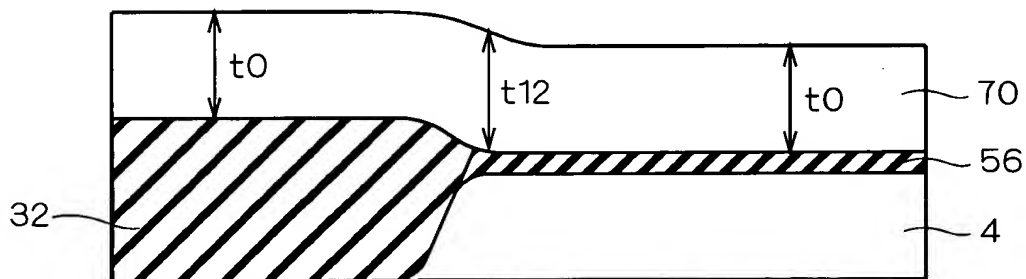


FIG. 59



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